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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China





STTA506D/F/B

TURBOSWITCH™ ULTRA-FAST HIGH VOLTAGE DIODE

MAIN PRODUCTS CHARACTERISTICS

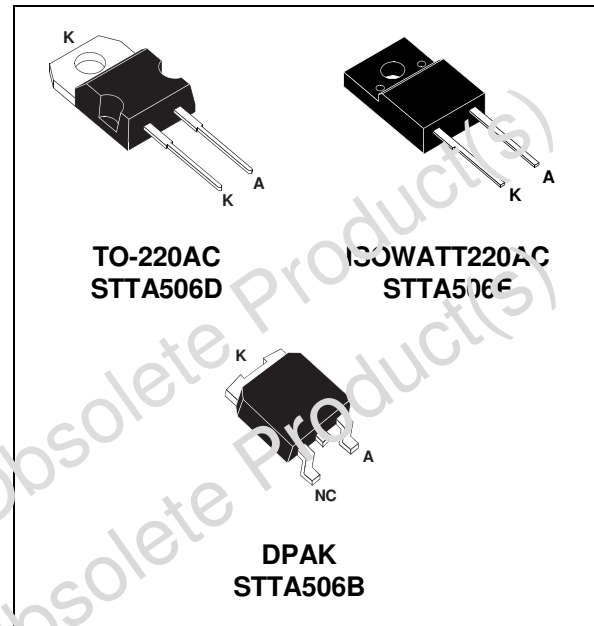
$I_{F(AV)}$	5A
V_{RRM}	600V
t_{rr} (typ)	20ns
V_F (max)	1.5V

FEATURES AND BENEFITS

- SPECIFIC TO "FREEWHEEL MODE" OPERATIONS: FREEWHEEL OR BOOSTER DIODE
- ULTRA-FAST AND SOFT RECOVERY
- VERY LOW OVERALL POWER LOSSES IN BOTH THE DIODE AND THE COMPANION TRANSISTOR
- HIGH FREQUENCY OPERATIONS
- INSULATED PACKAGE : ISOWATT220AC
Electrical insulation : 2000VDC
Capacitance < 12 pF

DESCRIPTION

The TURBOSWITCH is a very high performance series of ultra-fast high voltage power diodes from 600V to 1200V. TURBOSWITCH family, drastically cuts losses in both the diode and the associated switching IGBT or MOSFET in all "freewheel mode" operations



and is particularly suitable and efficient in motor control freewheel applications and in booster diode applications in power factor control circuitries. Packaged either in TO-220AC, ISOWATT220AC or in DPAK, these 600V devices are particularly intended for use on 240V domestic mains.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		600	V
V_{RSM}	Non repetitive peak reverse voltage		600	V
$I_{F(RMS)}$	RMS forward current	TO-220AC ISOWATT220AC	20	A
		DPAK	10	A
I_{FRM}	Repetitive peak forward current	$t_p=5\mu s$ $F=5kHz$ square	65	A
I_{FSM}	Surge non repetitive forward current	$t_p=10$ ms sinusoidal	55	A
T_j	Maximum operating junction temperature		150	°C
T_{stg}	Storage temperature range		-65 to 150	°C

TM : TURBOSWITCH is a trademark of STMicroelectronics

STTA506D/F/B**THERMAL AND POWER DATA**

Symbol	Parameter	Test conditions		Value	Unit
$R_{th(j-c)}$	Junction to case	TO-220AC / DPAK ISOWATT220AC		3.5 6.0	°C/W
P_1	Conduction power dissipation • $I_{F(AV)} = 5A$ $\delta = 0.5$	TO-220AC / DPAK ISOWATT220AC	$T_c = 118^\circ C$ $T_c = 96^\circ C$	9	W
P_{max}	Total power dissipation $P_{max} = P_1 + P_3$ ($P_3 = 10\% P_1$)	TO-220AC / DPAK ISOWATT220AC	$T_c = 115^\circ C$ $T_c = 90^\circ C$	10	W

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions		Min	Typ	Max	Unit
V_F^*	Forward voltage drop	$I_F = 5A$	$T_j = 25^\circ C$ $T_j = 125^\circ C$			1.75 1.5	V V
I_R^{**}	Reverse leakage current	$V_R = 0.8 \times V_{RRM}$	$T_j = 25^\circ C$ $T_j = 125^\circ C$			100 2	μA mA
V_{to}	Threshold voltage	$I_p < 3.1A_V$	$T_j = 125^\circ C$			1.15	V
r_d	Dynamic resistance					70	m Ω

Test pulse : * $t_p = 380 \mu s$, $\delta < 2\%$ ** $t_p = 5 ms$, $\delta < 2\%$

To evaluate the maximum conduction losses use the following equation :

$$P = V_{to} \times I_{F(AV)} + r_d \times I_F^2(RMS)$$

DYNAMIC ELECTRICAL CHARACTERISTICS**TURN-OFF SWITCHING**

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
t_{rr}	Reverse recovery time	$T_j = 25^\circ C$ $I_F = 0.5 A$ $I_R = 1 A$ $I_{rr} = 0.25 A$ $I_F = 1 A$ $di_F/dt = -50 A/\mu s$ $V_R = 30 V$		20	50	ns
I_{RM}	Maximum reverse recovery current	$T_j = 125^\circ C$ $V_R = 400 V$ $I_F = 5 A$ $di_F/dt = -40 A/\mu s$ $di_F/dt = -500 A/\mu s$		11	3.0	A
S factor	Softness factor	$T_j = 125^\circ C$ $V_R = 400 V$ $I_F = 5 A$ $di_F/dt = -500 A/\mu s$		0.55		-

TURN-ON SWITCHING

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
t_{fr}	Forward recovery time	$T_j = 25^\circ C$ $I_F = 5 A$, $di_F/dt = 40 A/\mu s$ measured at $1.1 \times V_{Fmax}$			500	ns
V_{Fp}	Peak forward voltage	$T_j = 25^\circ C$ $I_F = 5 A$, $di_F/dt = 40 A/\mu s$			10	V

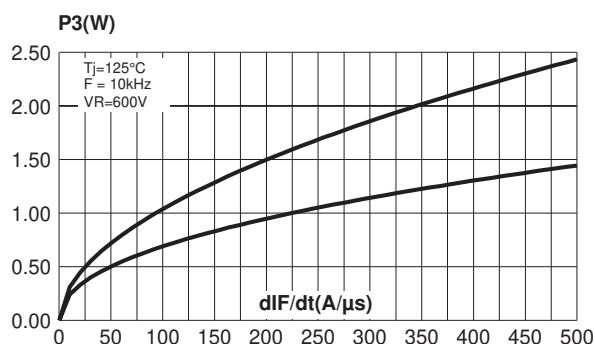
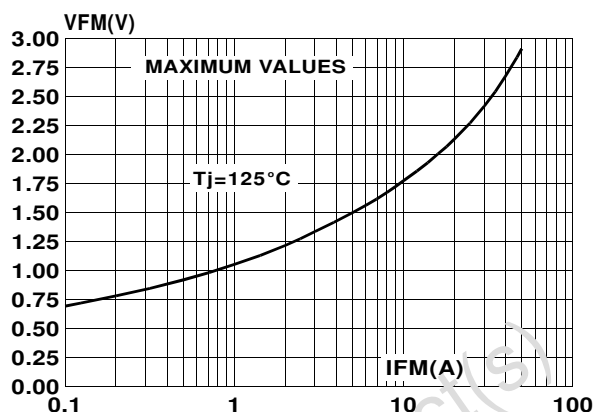
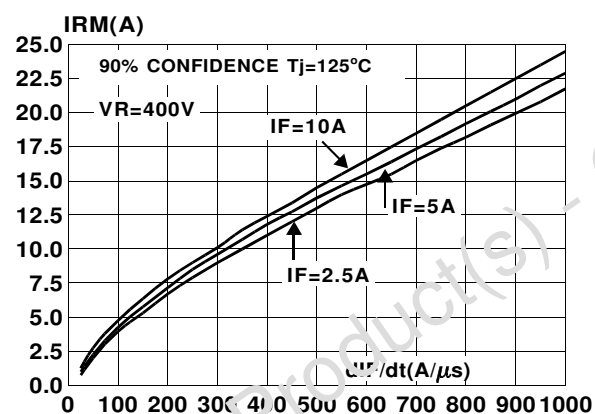
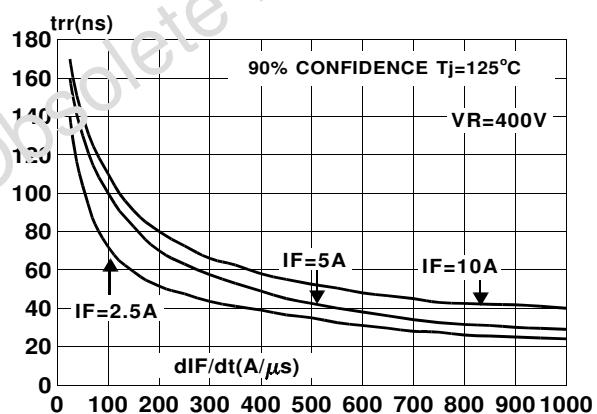
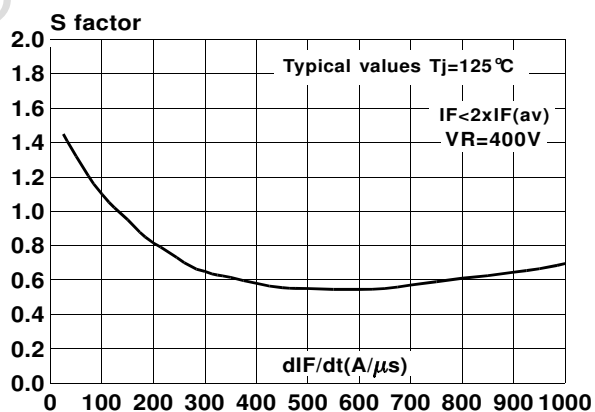
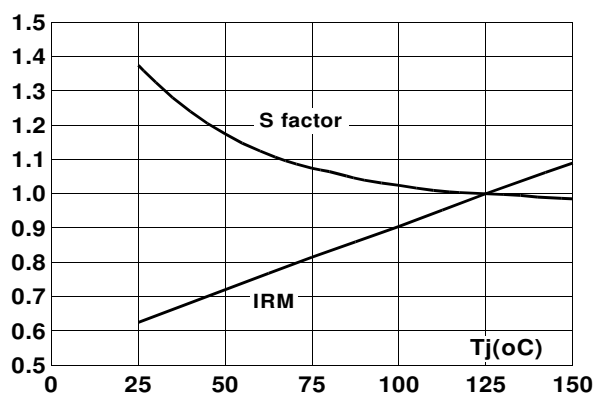
Fig. 1: Switching OFF losses versus di/dt .**Fig. 2:** Forward voltage drop versus forward current.**Fig. 3:** Peak reverse recovery current versus di/dt .**Fig. 4:** Reverse recovery time versus di/dt .**Fig. 5:** Switching factor (t_b/t_a) versus di/dt .**Fig. 6:** Relative variation of dynamic parameters versus junction temperature (reference $T_j = 125^\circ\text{C}$).

Fig. 7: Transient peak forward voltage versus di_F/dt .

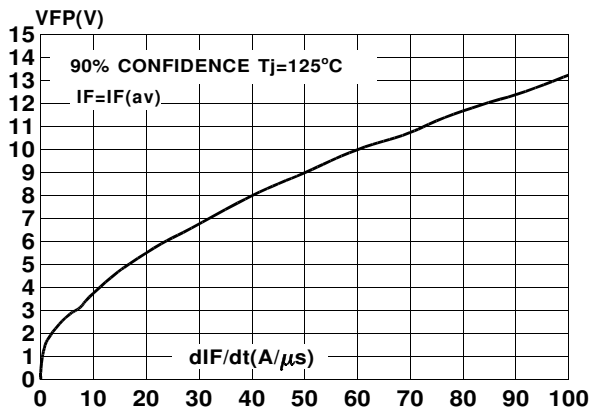


Fig. 8: Forward recovery time versus di_F/dt .

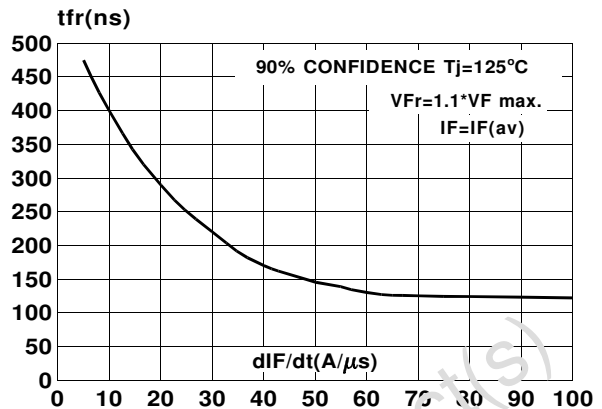


Fig. 9: Relative variation of thermal transient impedance junction to case versus pulse duration (TO-220AC and DPAK).

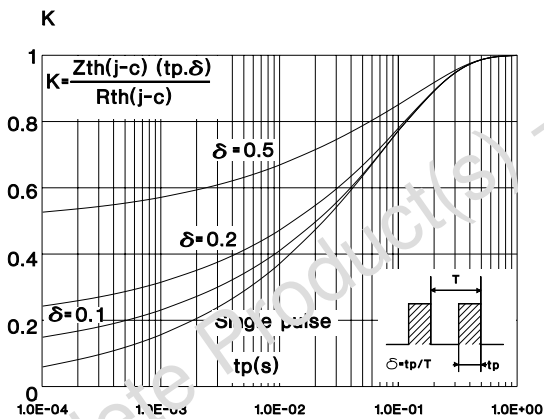
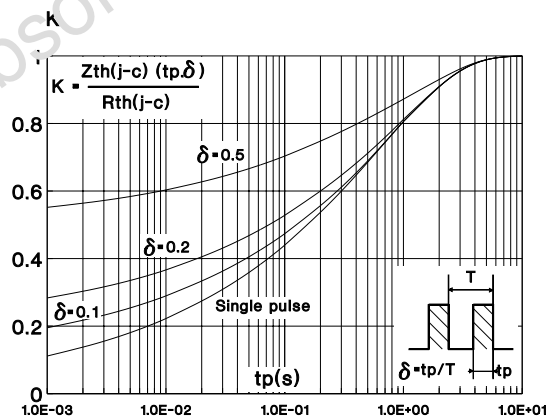


Fig. 10: Relative variation of thermal transient impedance junction to case versus pulse duration (ISOWATT220AC).



APPLICATION DATA

The TURBOSWITCH is especially designed to provide the lowest overall power losses in any "FREEWHEEL Mode" application (Fig.A) considering both the diode and the companion transistor, thus optimizing the overall performance in the end application.

The way of calculating the power losses is given below:

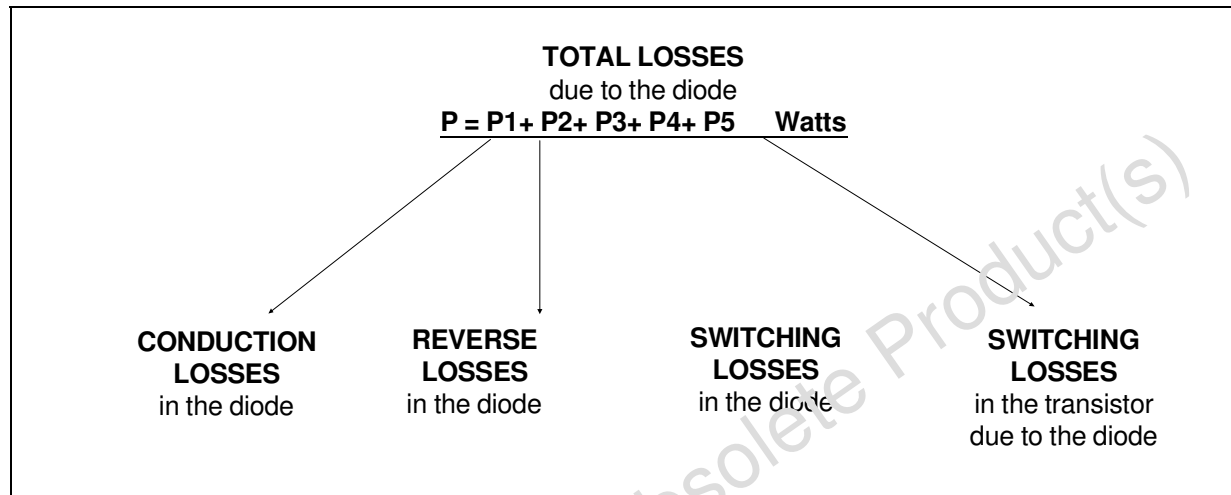
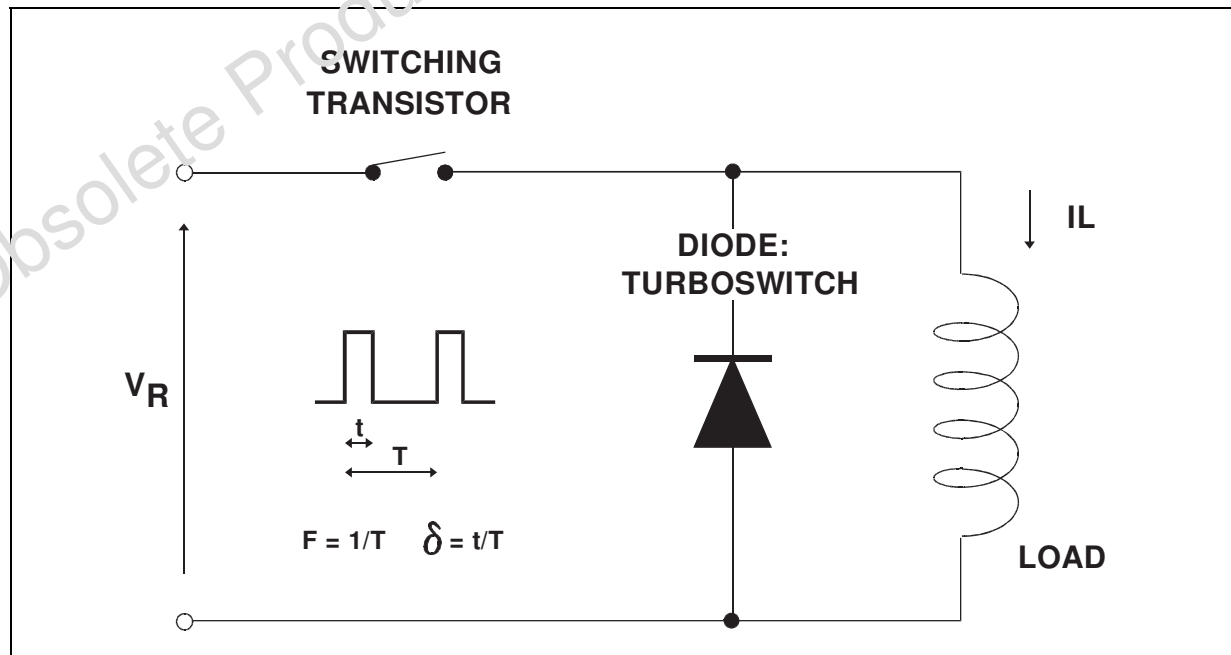
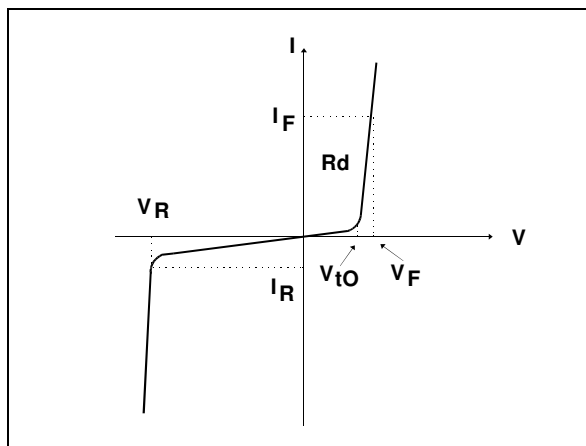


Fig. A : "FREEWHEEL" MODE



APPLICATION DATA (Cont'd)

Fig. B : STATIC CHARACTERISTICS

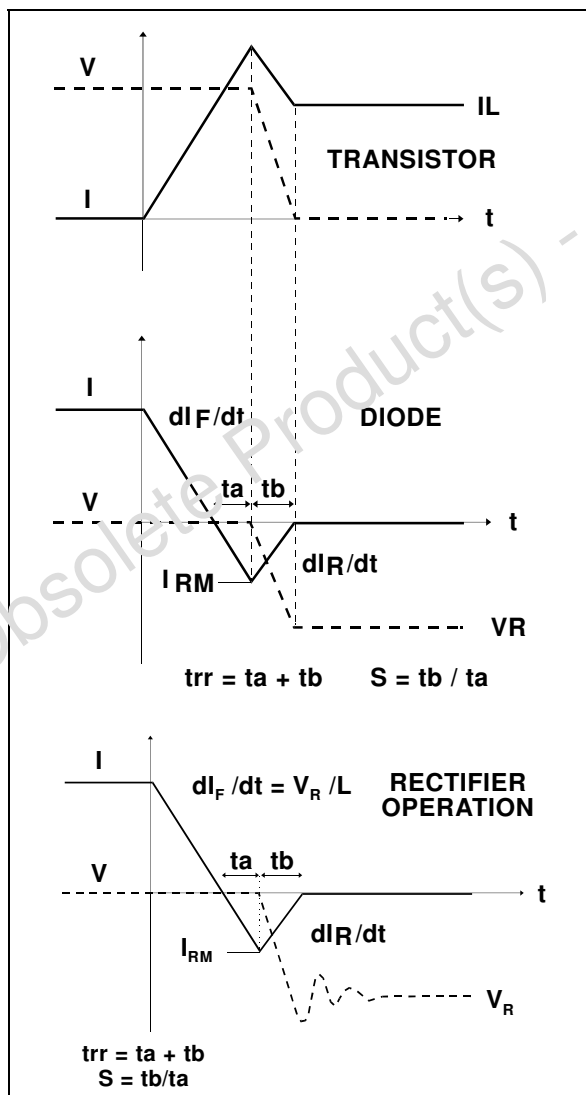
**Conduction losses :**

$$P1 = V_{t0} \cdot I_F(AV) + R_d \cdot I_F^2(RMS)$$

Reverse losses :

$$P2 = V_R \cdot I_R \cdot (1 - \delta)$$

Fig. C : TURN-OFF CHARACTERISTICS

**Turn-on losses**
(in the transistor, due to the diode)

$$P5 = \frac{V_R \times I_{RM}^2 \times (3 + 2 \times S) \times F}{6 \times dI_F/dt} + \frac{V_R \times I_{RM} \times I_L \times (S + 2) \times F}{2 \times dI_F/dt}$$

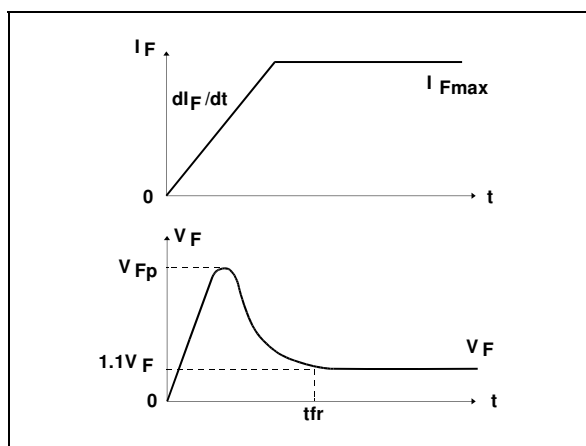
Turn-off losses (in the diode) :

$$P3 = \frac{V_R \times I_{RM}^2 \times S \times F}{6 \times dI_F/dt}$$

P3 and P5 are suitable for power MOSFET and IGBT

APPLICATION DATA (Cont'd)

Fig. D : TURN-ON CHARACTERISTICS

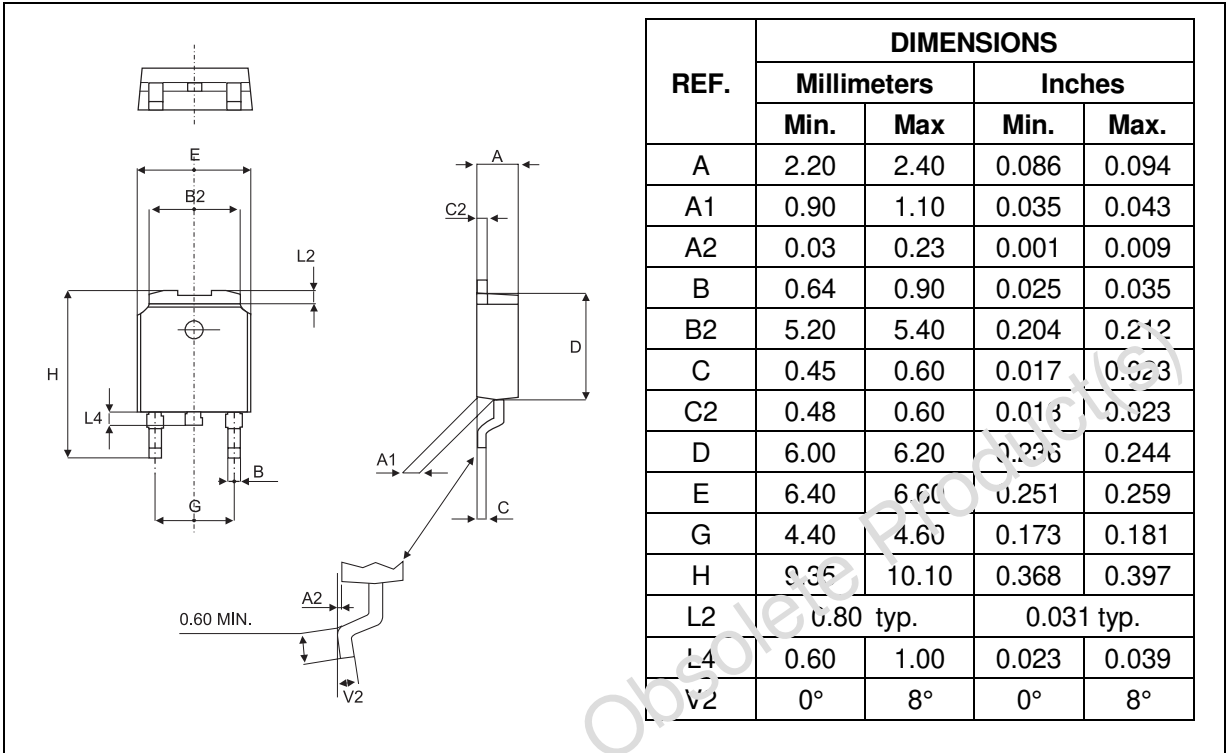


Turn-on losses :

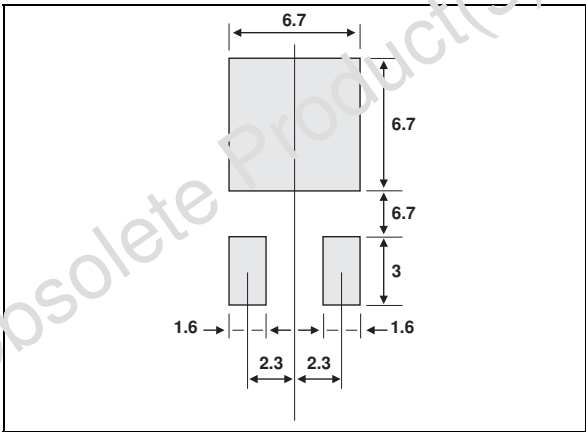
$$P_4 = 0.4 (V_{FP} - V_F) \cdot I_{Fmax} \cdot t_{fr} \cdot F$$

STTA506D/F/B

PACKAGE MECHANICAL DATA
DPAK

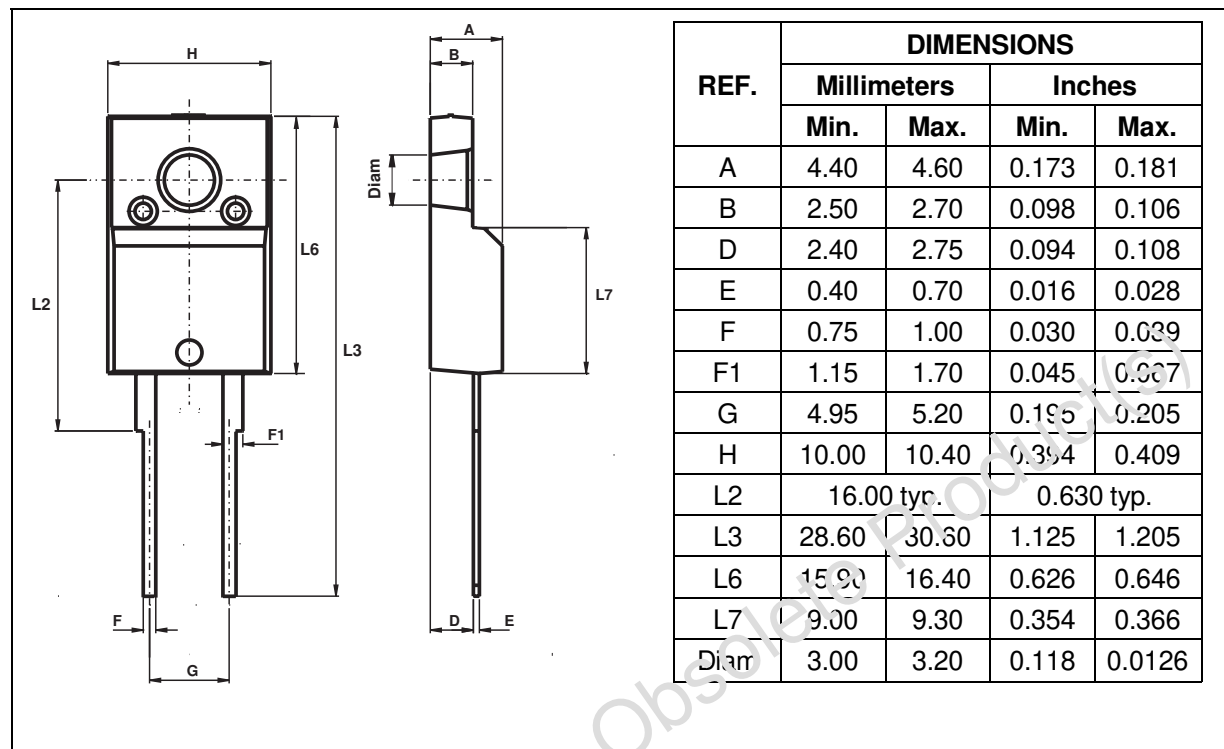


FOOTPRINT DIMENSIONS (in millimeters)



■ Cooling method : by conduction (C)

PACKAGE MECHANICAL DATA
ISOWATT220AC



- Cooling method : by conduction (C)
- Recommended torque value : 0.55m.N
- Maximum torque value : 0.7m.N

STTA506D/F/B**PACKAGE MECHANICAL DATA**

TO-220AC

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
C	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
E	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
H2	10.00	10.40	0.393	0.409
L2	16.40 typ.		0.645 typ.	
L4	13.00	14.00	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	3.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
M	2.6 typ.		0.102 typ.	
Diam. I	3.75	3.85	0.147	0.151

- Cooling method : by conduction (C)
- Recommended torque value : 0.55m.N
- Maximum torque value : 0.7m.N

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STTA506D	STTA506D	TO-220AC	1.86g	50	Tube
STTA506F	STTA506F	ISOWATT220AC	2g	50	Tube
STTA506B	STTA506B	DPAK	0.3g	75	Tube
STTA506B-TR	STTA506B	DPAK	0.3g	2500	Tape & reel

- Epoxy meets UL94,V0

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